

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4633	(438/3,264,526,591,954).OCLs.	US-PGRUB; USPAT; EPO; DERWENT	OR	OFF	2007/12/13 11:09
L2	692	L1 and "nonvolatile memory"	US-PGRUB; USPAT; EPO; DERWENT	OR	OFF	2007/12/13 11:10
L3	192	L2 and (ono o-n-o "oxide-nitride-oxide")	US-PGRUB; USPAT; EPO; DERWENT	OR	OFF	2007/12/13 11:11
L4	71	L3 and @ad<"20010115"	US-PGRUB; USPAT; EPO; DERWENT	OR	OFF	2007/12/13 11:11
L5	55232	"nonvolatile memory"	US-PGRUB; USPAT; EPO; DERWENT	OR	OFF	2007/12/13 11:21
L6	3224	L5 and (ono o-n-o "oxide-nitride-oxide")	US-PGRUB; USPAT; EPO; DERWENT	OR	OFF	2007/12/13 11:21
L7	636	L6 and @ad<"20010115"	US-PGRUB; USPAT; EPO; DERWENT	OR	OFF	2007/12/13 11:21
L8	230	L7 and ("control gate" "control layer") near5 (polysilicon "doped polysilicon")	US-PGRUB; USPAT; EPO; DERWENT	OR	OFF	2007/12/13 11:24
L9	133	L8 and ("word line" "bit line")	US-PGRUB; USPAT; EPO; DERWENT	OR	OFF	2007/12/13 11:27
S24	2	("20050121714").PN.	US-PGRUB; USPAT; EPO; DERWENT	OR	OFF	2007/12/13 10:00

12/13/07 11:35:31 AM

C:\Documents and Settings\wlouie\My Documents\EAST\Workspaces\Memory Device.wsp